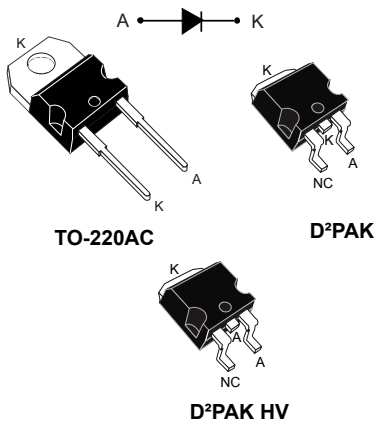


Automotive 650 V, 12 A, silicon carbide power Schottky diode



Features

- AEC-Q101 qualified 
- No or negligible reverse recovery
- Switching behavior independent of temperature
- Dedicated to PFC applications
- High forward surge capability
- PPAP capable
- Operating T_j from -40 °C to 175 °C
- V_{RRM} guaranteed from -40 to $+175\text{ °C}$
- D²PAK HV creepage distance (anode to cathode) = 5.38 mm min. (with top coating)
- ECOPACK®2 compliant

Product label



Product status link

[STPSC12065-Y](#)

Product summary

$I_F(\text{AV})$	12 A
V_{RRM}	650 V
$T_j(\text{max.})$	175 °C
$V_F(\text{typ.})$	1.30 V

Applications

- On board charger

Description

The SiC diode is an ultra high performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, the [STPSC12065-Y](#) will boost performance in hard switching conditions. Its high forward surge capability ensures good robustness during transient phases.

1 Characteristics

Table 1. Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage ($T_j = -40\text{ °C}$ to $+175\text{ °C}$)		650	V
$I_{F(RMS)}$	Forward rms current		22	A
$I_{F(AV)}$	Average forward current	$T_c = 145\text{ °C}^{(1)}$, DC	12	A
I_{FRM}	Repetitive peak forward current	$T_c = 145\text{ °C}^{(1)}$, $T_j = 175\text{ °C}$, $\delta = 0.1$	53	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal, $T_c = 25\text{ °C}$	50	A
		$t_p = 10\text{ ms}$ sinusoidal, $T_c = 125\text{ °C}$	40	
		$t_p = 10\text{ }\mu\text{s}$ square, $T_c = 25\text{ °C}$	220	
T_{stg}	Storage temperature range		-55 to +175	°C
T_j	Operating junction temperature		-40 to +175	°C

1. Value based on $R_{th(j-c)}$ max.

Table 2. Thermal resistance parameters

Symbol	Parameter	Value		Unit
		Typ.	Max.	
$R_{th(j-c)}$	Junction to case	0.85	1.25	°C/W

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$	-	15	150	μA
		$T_j = 150\text{ °C}$		-	200	1000	
		$T_j = 25\text{ °C}$	$V_R = 600\text{ V}$		8	50	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 12\text{ A}$	-	1.30	1.45	V
		$T_j = 150\text{ °C}$		-	1.45	1.65	
		$T_j = 175\text{ °C}$		-	1.50		

1. Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$

2. Pulse test: $t_p = 500\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses, use the following equation:

$$P = 1.02 \times I_{F(AV)} + 0.065 \times I_{F(RMS)}^2$$

Table 4. Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$Q_{Cj}^{(1)}$	Total capacitive charge	$V_R = 400\text{ V}$	-	36	-	nC

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _j	Total capacitance	V _R = 0 V, T _c = 25 °C, F = 1 MHz	-	750	-	pF
		V _R = 400 V, T _c = 25 °C, F = 1 MHz	-	60	-	

1. *Most accurate value for the capacitive charge:* $Q_{cj}(V_R) = \int_0^{V_R} C_j(V) dV$

1.1 Characteristics (curves)

Figure 1. Forward voltage drop versus forward current (typical values)

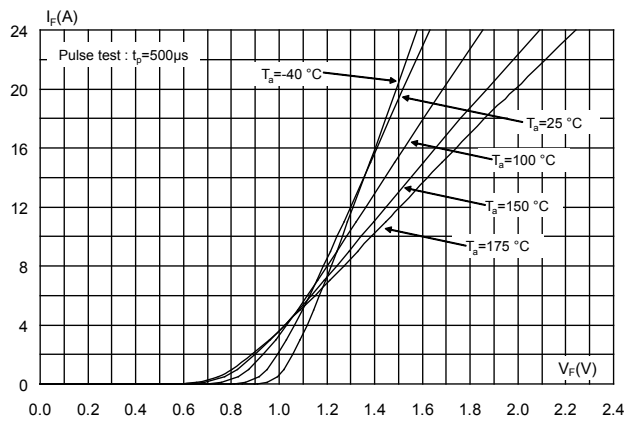


Figure 2. Reverse leakage current versus reverse voltage applied (typical values)

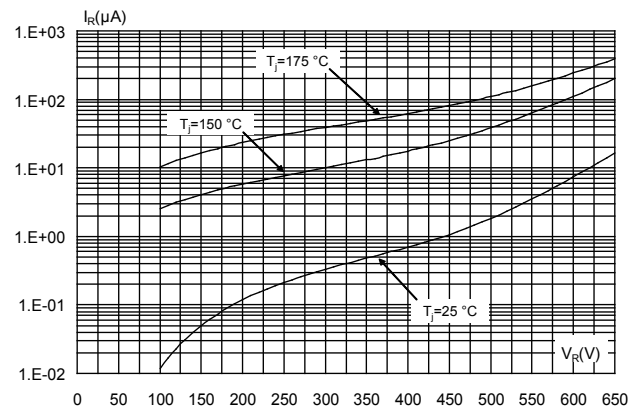


Figure 3. Peak forward current versus case temperature

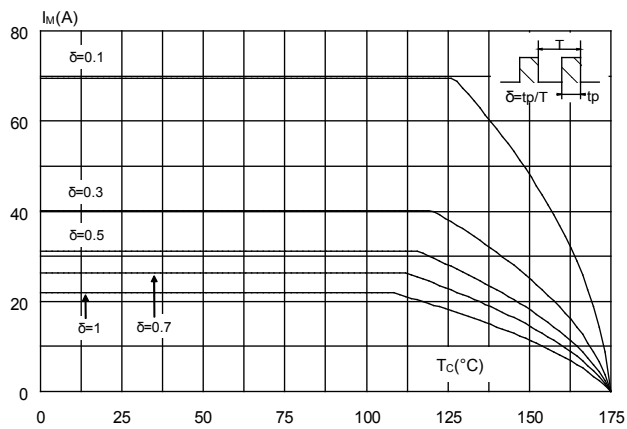


Figure 4. Junction capacitance versus reverse voltage applied (typical values)

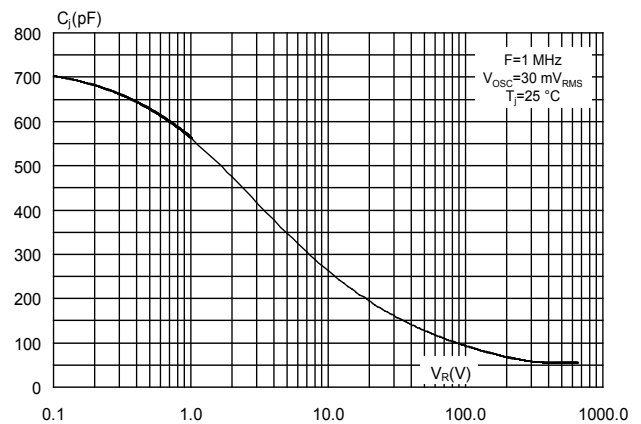


Figure 5. Relative variation of thermal impedance junction to case versus pulse duration

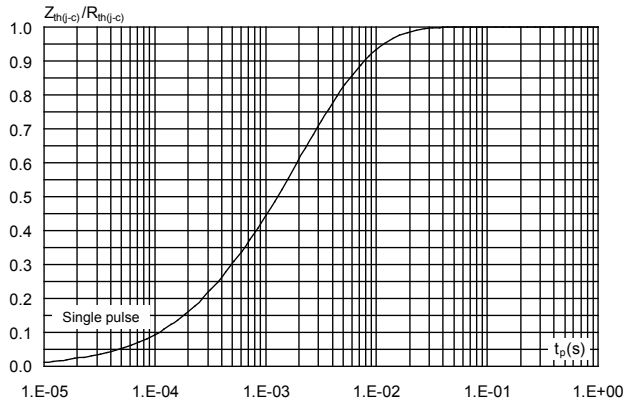


Figure 6. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)

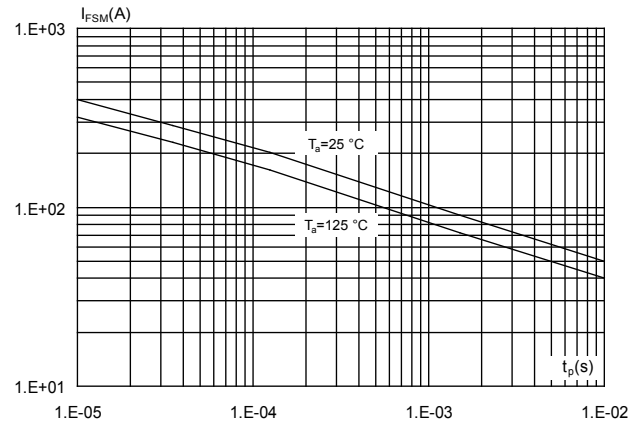


Figure 7. Total capacitive charges versus reverse voltage applied (typical values)

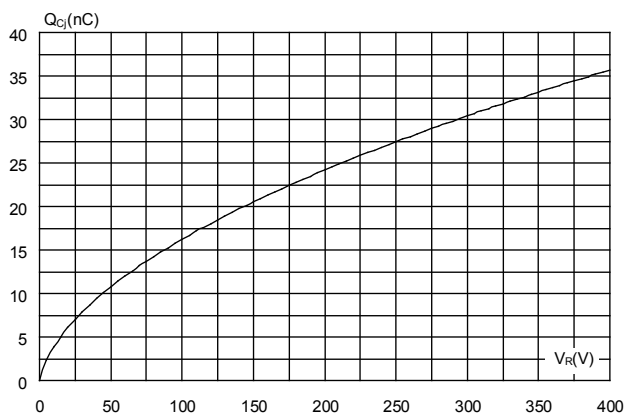
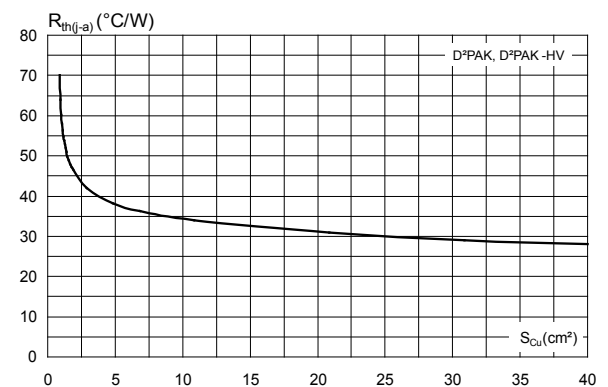


Figure 8. Thermal resistance junction to ambient versus copper surface under tab (typical values, epoxy printed board FR4, $e_{Cu} = 35\text{ }\mu m$)



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK®** packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 TO-220AC package information

- Epoxy meets UL 94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.70 N·m

Figure 9. TO-220AC package outline

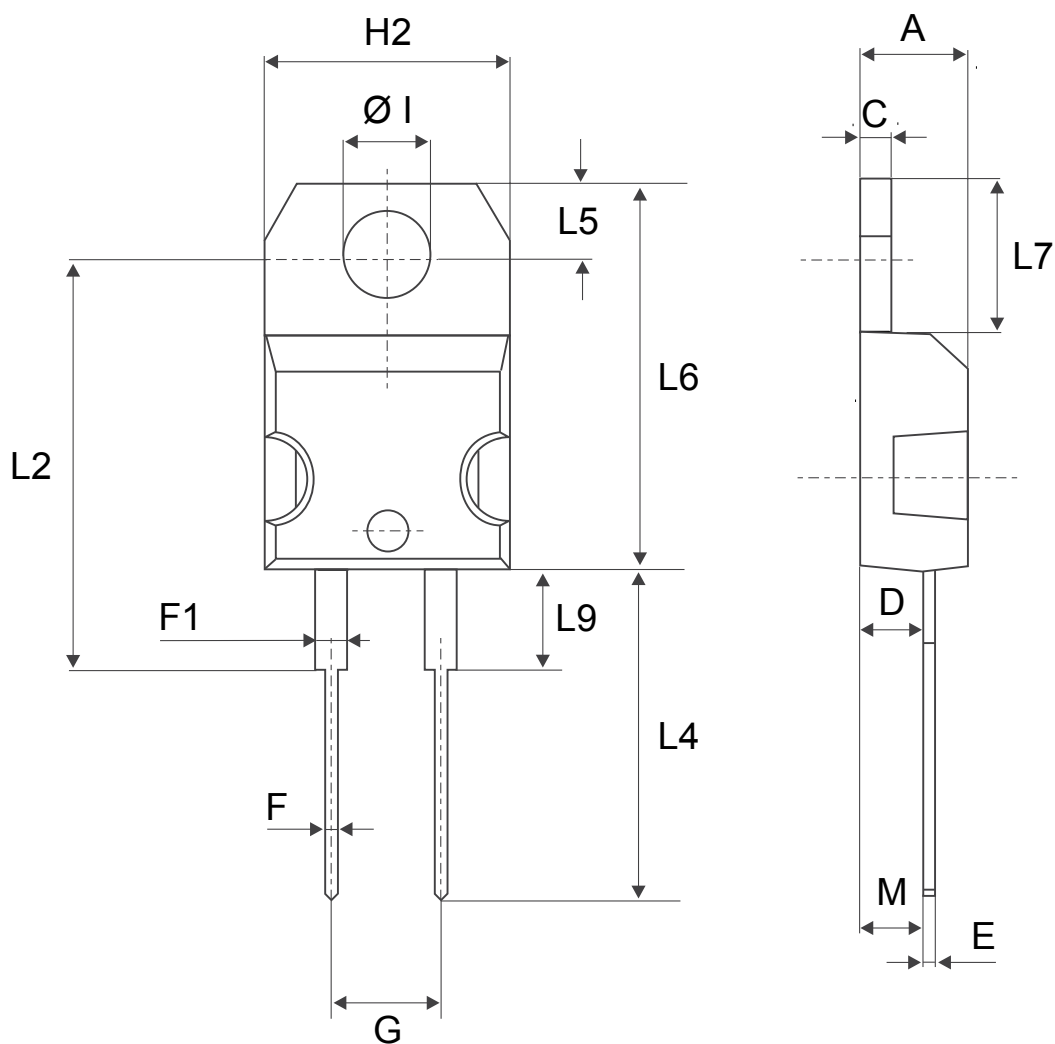


Table 5. TO-220AC package mechanical data

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40 typ.		0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
ØI	3.75	3.85	0.147	0.151

2.2 D²PAK package information

- Epoxy meets UL94, V0.
- Cooling method: by conduction (C)

Figure 10. D²PAK package outline

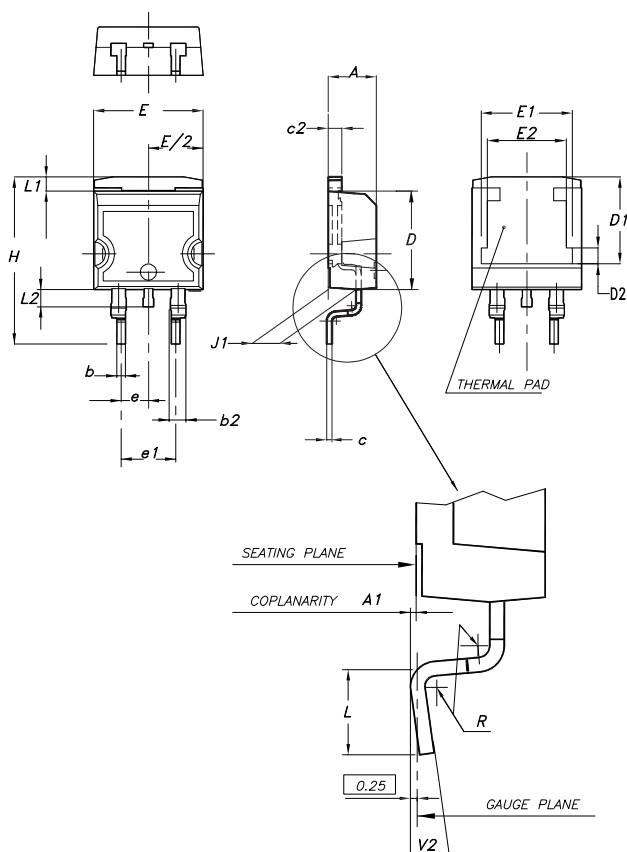
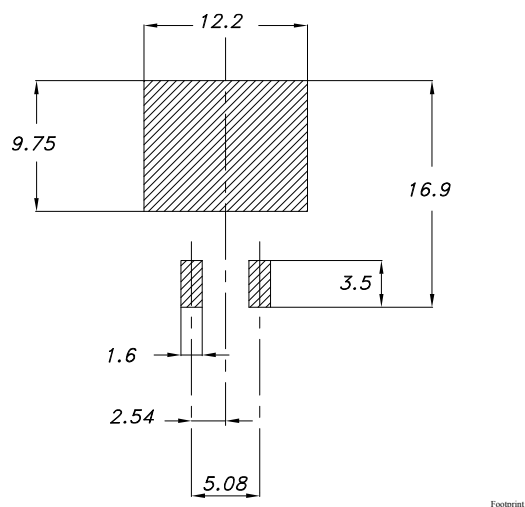


Table 6. D²PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.028		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.018		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50	7.75	8.00	0.295	0.305	0.315
D2	1.10	1.30	1.50	0.043	0.051	0.060
E	10		10.40	0.394		0.409

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
E1	8.30	8.50	8.70	0.326	0.335	0.343
E2	6.85	7.05	7.25	0.266	0.278	0.282
e		2.54			0.100	
e1	4.88		5.28	0.190		0.205
H	15		15.85	0.591		0.624
J1	2.49		2.69	0.097		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.049		0.055
L2	1.30		1.75	0.050		0.069
R		0.4			0.015	
V2	0°		8°	0°		8°

Figure 11. D²PAK recommended footprint (dimensions are in mm)



2.3 D²PAK high voltage package information

Figure 12. D²PAK high voltage package outline

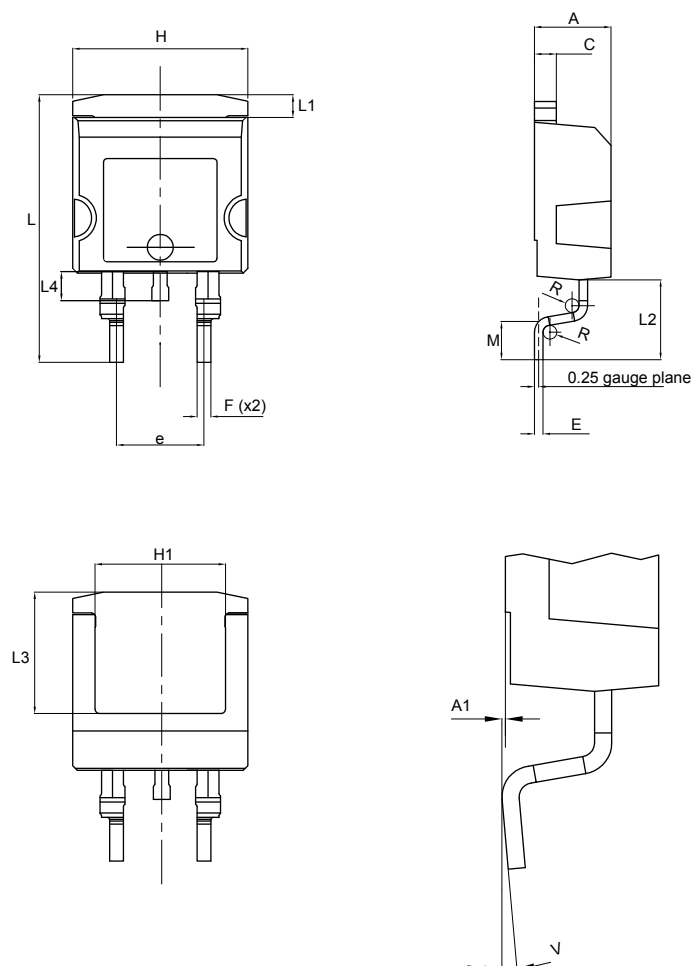
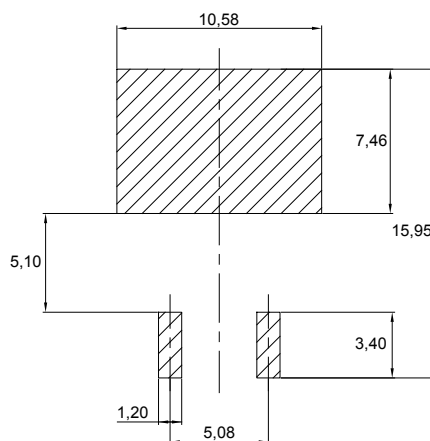


Table 7. D²PAK high voltage package mechanical data

Ref.	Dimensions		
	Min.	Typ.	Max.
A	4.30		4.70
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

Figure 13. D²PAK High Voltage footprint in mm


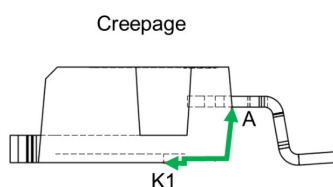
2.3.1 Creepage distance between Anode and Cathode

Table 8. Creepage distance between anode and cathode

Symbol	Parameter		Value	Unit
Cd _{A-K1}	Minimum creepage distance between A and K1 (with top coating)	D ² PAK HV	5.38	mm
Cd _{A-K2}	Minimum creepage distance between A and K2 (without top coating)		3.48	

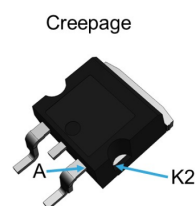
Note: D²PAK HV creepage distance (anode to cathode) = 5.38 mm min. (refer to IEC 60664-1)

Figure 14. Creepage with top coating



Minimum distance between A & K1 = 5.38 mm (with top coating)

Figure 15. Creepage without top coating



Minimum distance between A & K2 = 3.48 mm (without top coating)

3 Ordering information

Table 9. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC12065DY	PSC12065DY	TO-220AC	1.86 g	50	Tube
STPSC12065GY-TR	PSC12065GY	D ² PAK	1.48 g	1000	Tape and reel
STPSC12065G2Y-TR	PSC12065G2Y	D ² PAK HV	1.48 g	1000	Tape and reel

Revision history

Table 10. Document revision history

Date	Revision	Changes
10-May-2016	1	First issue.
06-Nov-2017	2	Added D ² PAK package.
10-Sep-2018	3	Added D ² PAK HV package.
04-Dec-2018	4	Updated Section 2.3.1 Creepage distance between anode and cathode . Minor text changes to improve readability. Updated title of document.

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